

FIG. 1
PRIOR ART

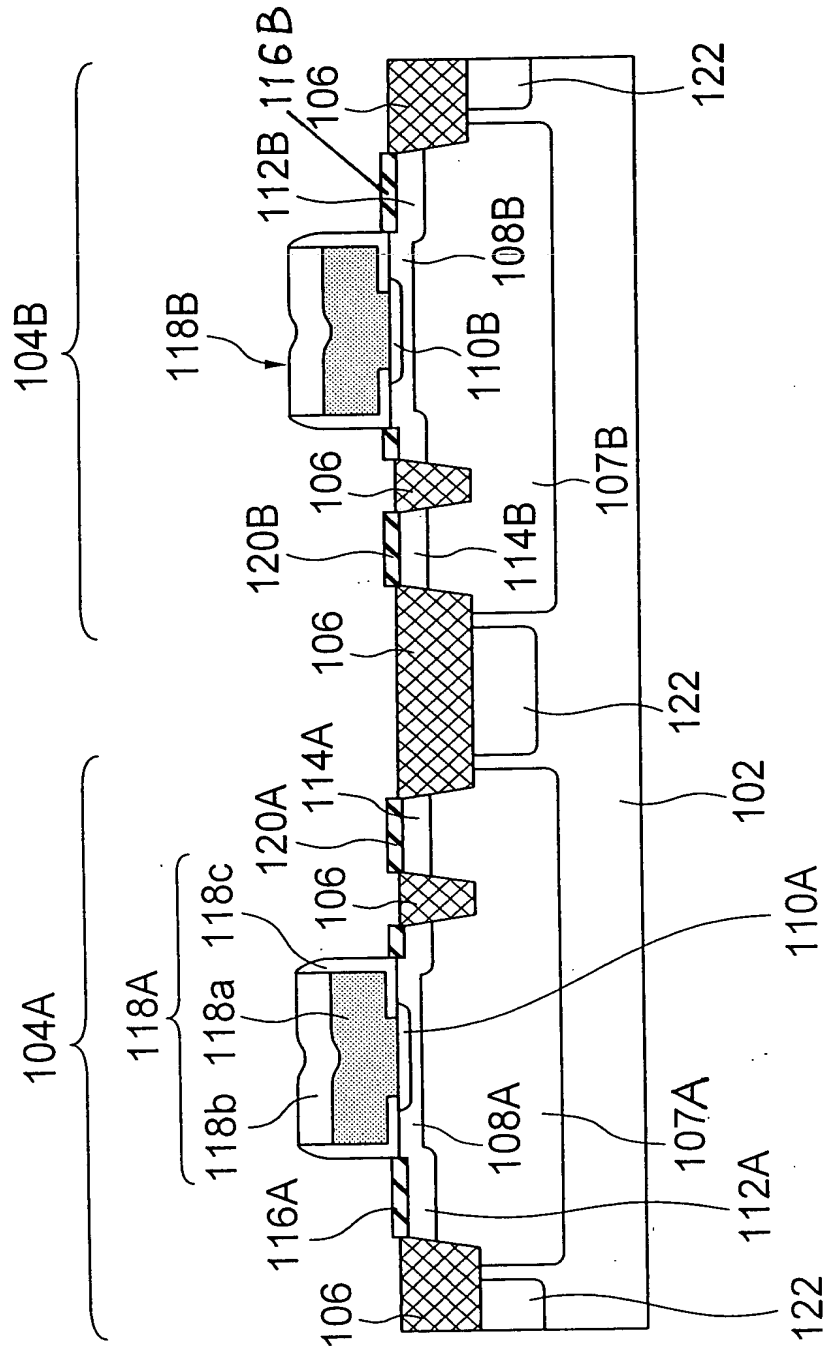


FIG. 2
PRIOR ART

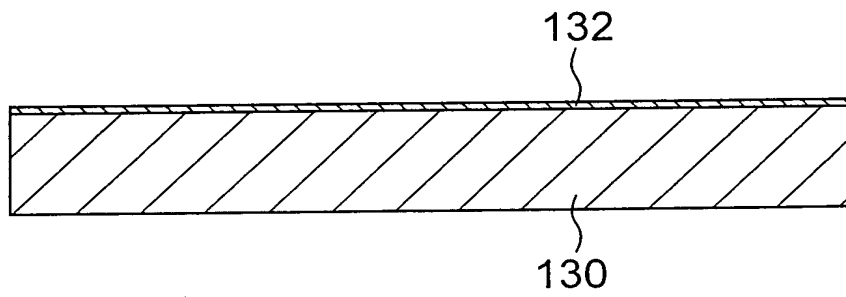


FIG. 3A

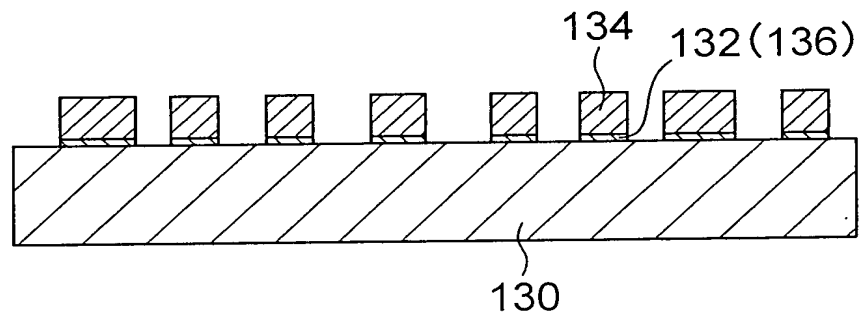


FIG. 3B

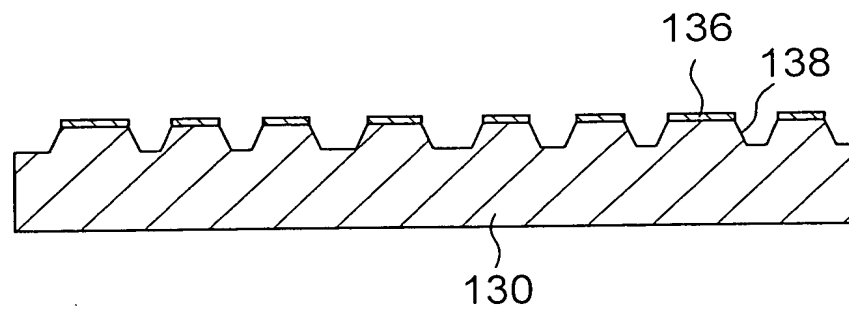


FIG. 3C

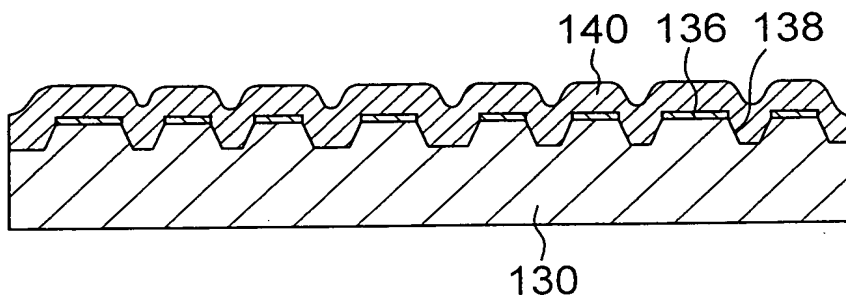


FIG. 3D

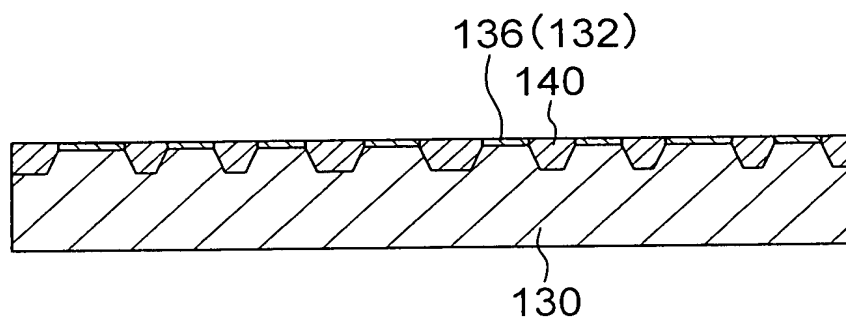


FIG. 3E

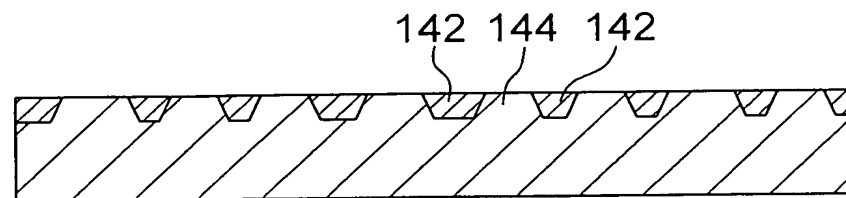


FIG. 3F

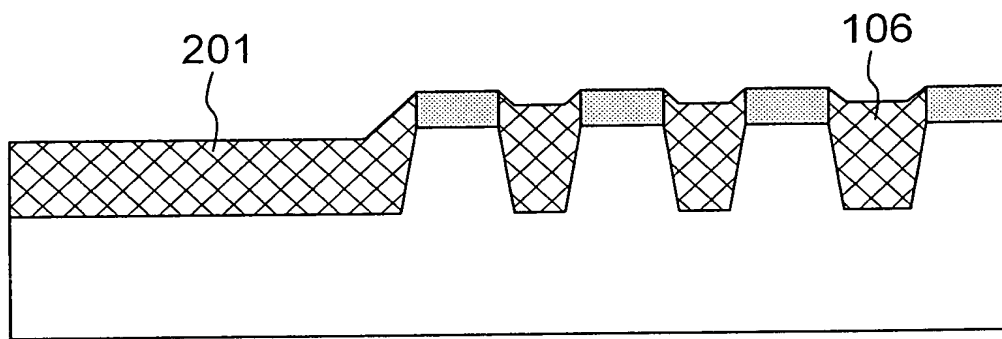


FIG. 4A

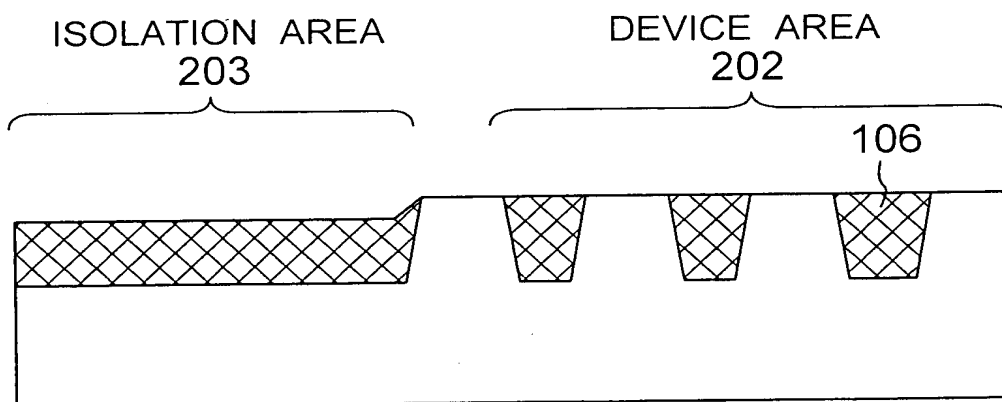


FIG. 4B

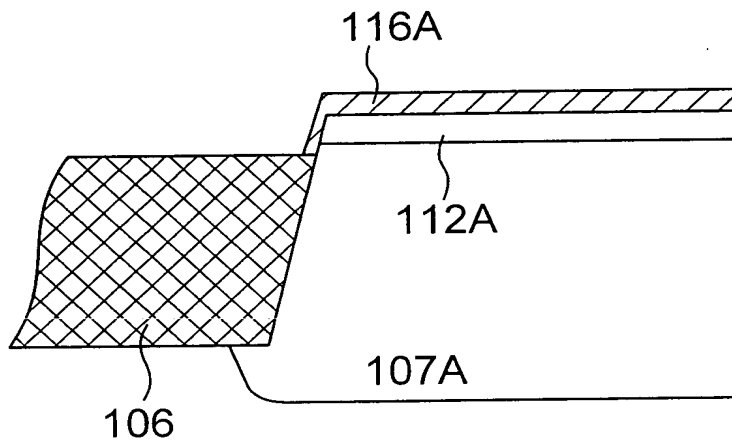


FIG. 5A

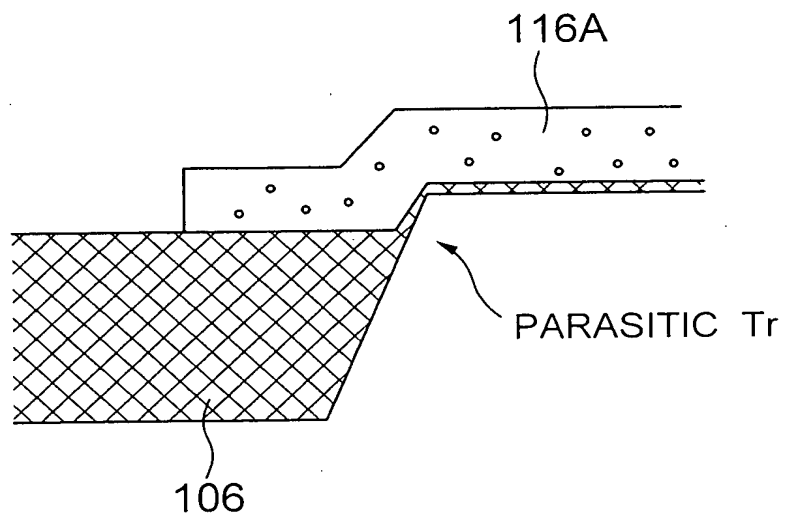


FIG. 5B

[illegible]

A cross-sectional view of a semiconductor device. A central gate structure (206) is positioned on a substrate (209). The gate structure is flanked by side spacers (207). The entire device is covered by a top layer (205). The substrate (209) is divided into two regions (202 and 203) by a central channel (210). The side spacers (207) are located in the channel region (210). The top layer (205) is divided into two regions (202 and 203) by a central channel (210). The side spacers (207) are located in the channel region (210).

FIG. 6B

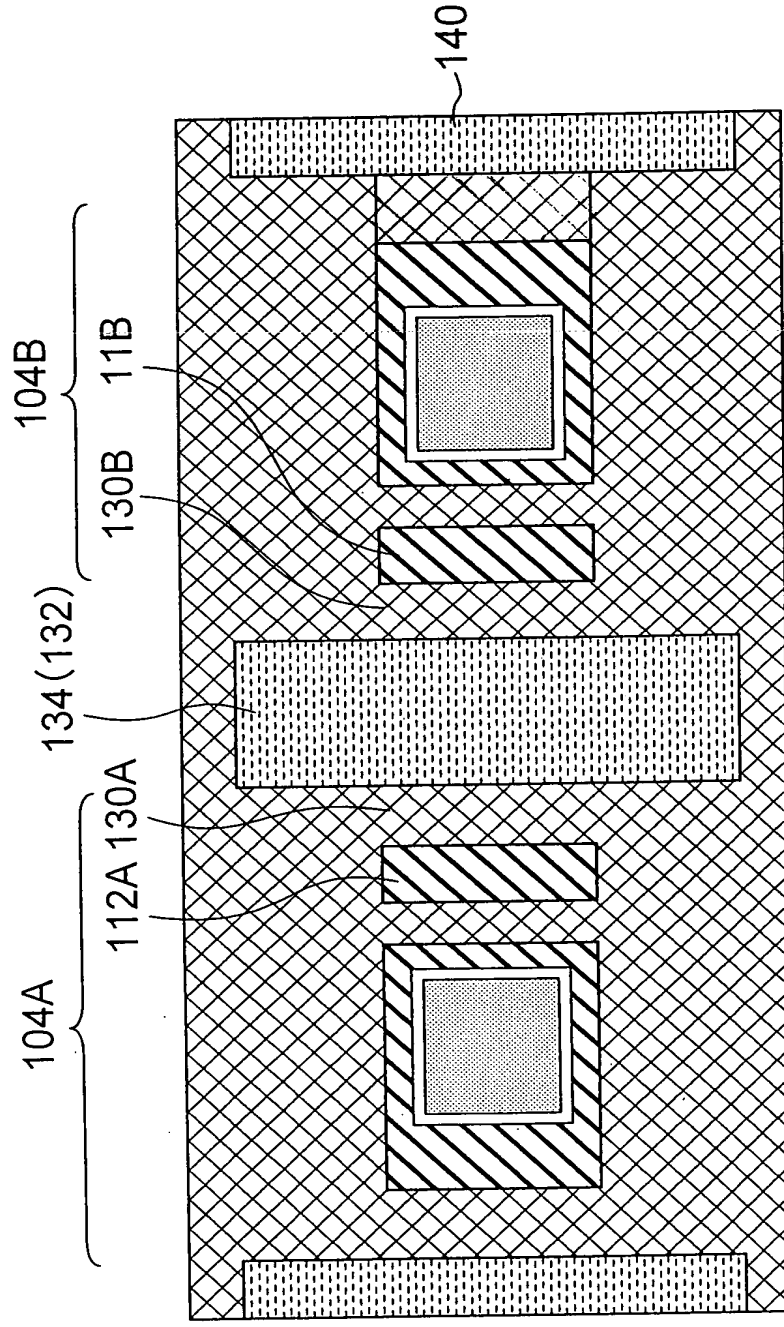


FIG. 7

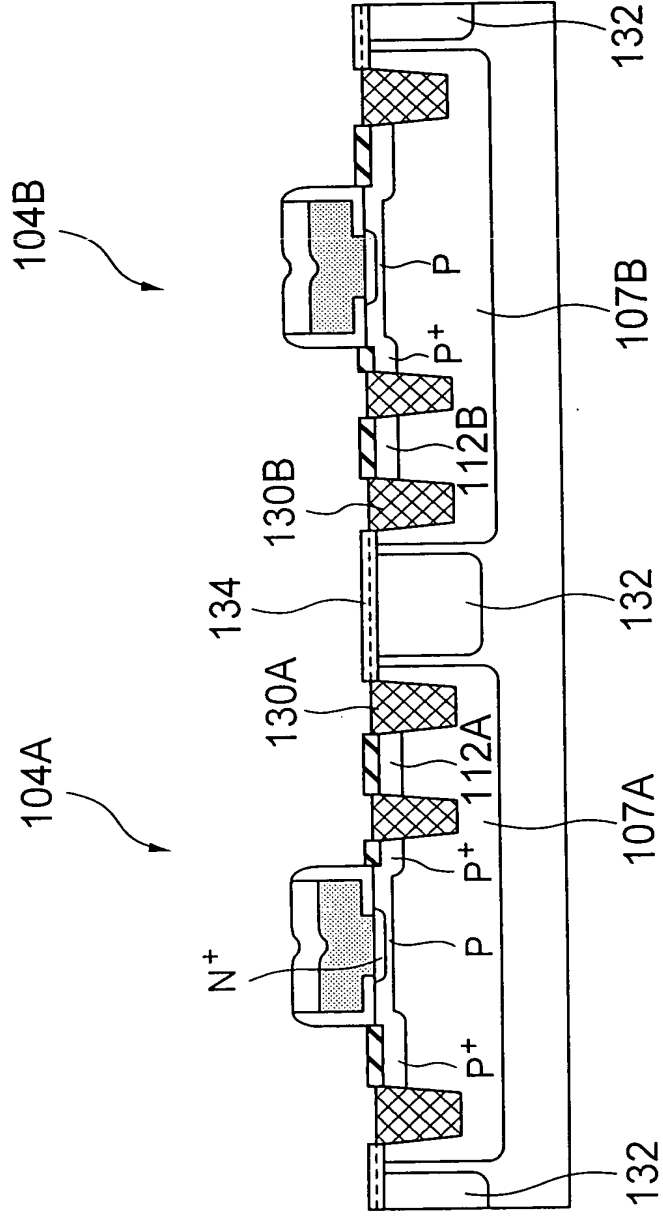


FIG. 8

A cross-sectional view of a semiconductor device 10. The device consists of a substrate 20a with a cross-hatched pattern. A layer 20b is formed on the substrate 20a. Within layer 20b, there is a central region 36 with a stippled pattern, surrounded by a region 38 with diagonal hatching. A layer 30 is formed on top of region 38. A layer 21 (39) is formed on top of layer 30. A bracket 12 indicates the width of the device. A dimension line 28 is shown at the bottom, and a dimension line 36 is shown at the bottom left.

FIG. 9

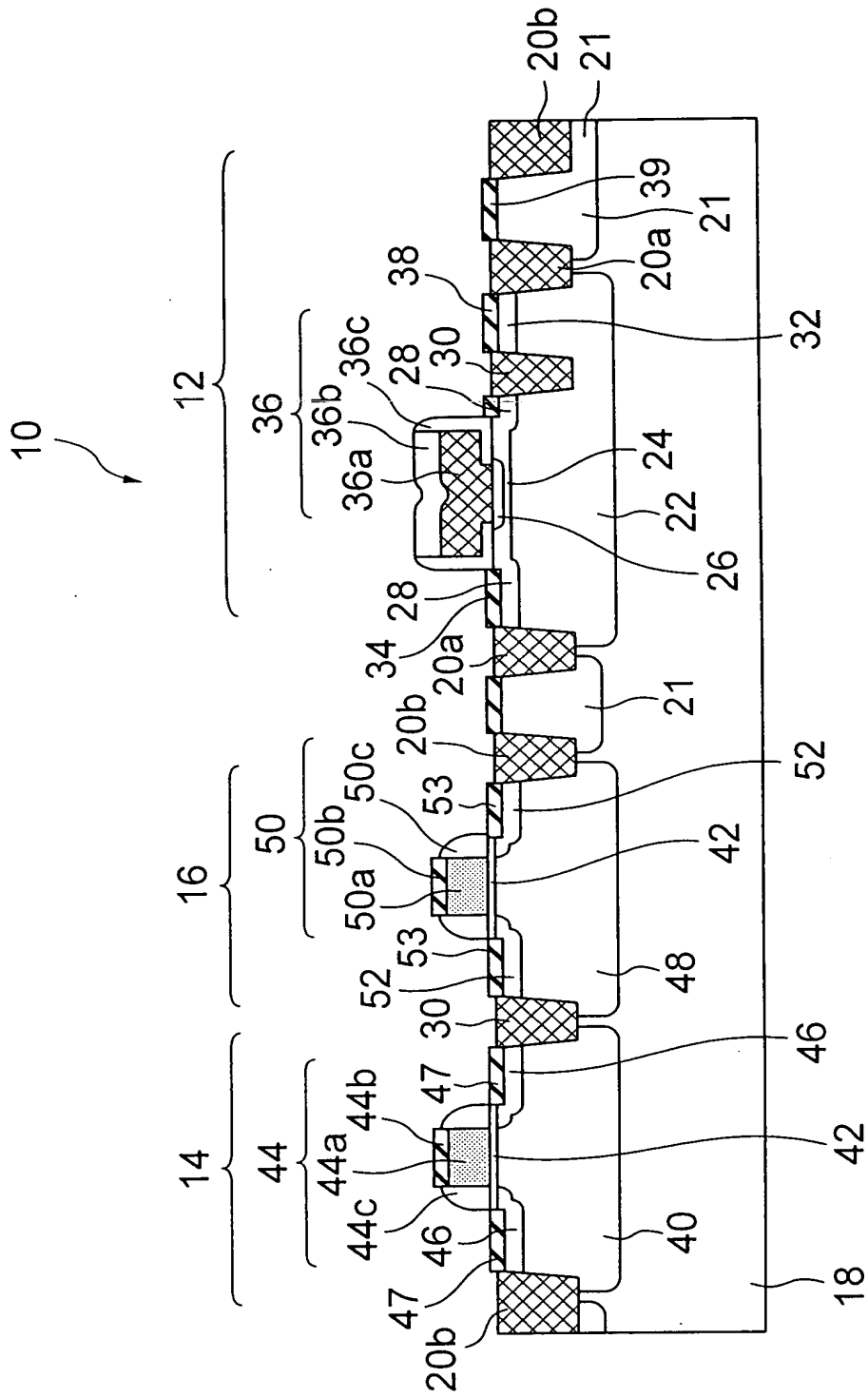


FIG. 10

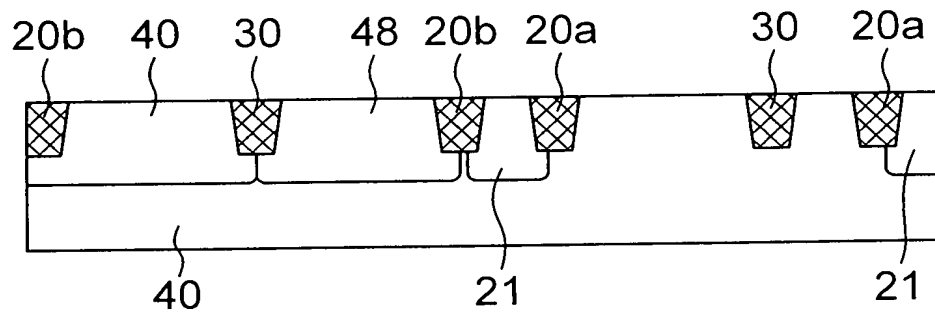


FIG. 11A

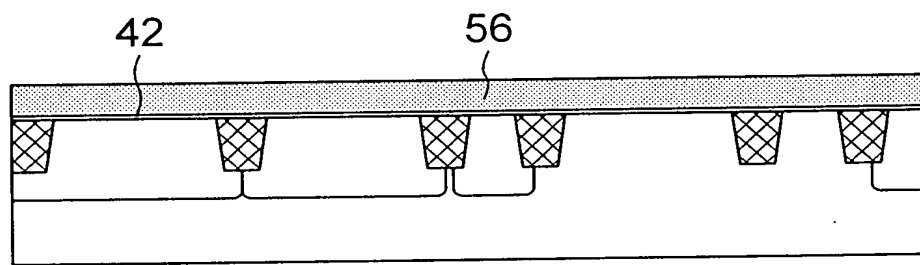


FIG. 11B

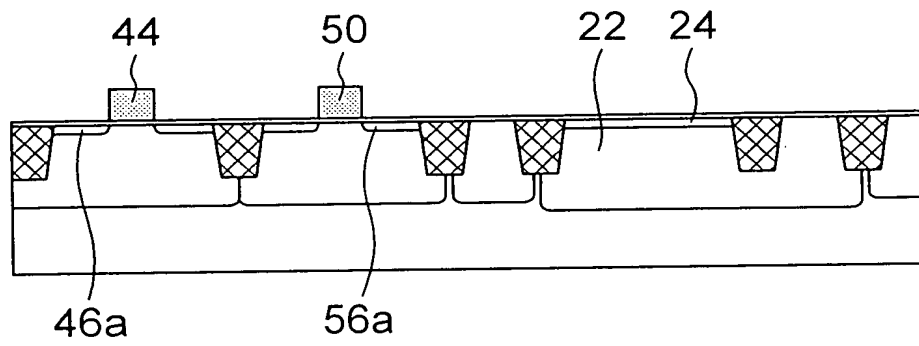


FIG. 11C

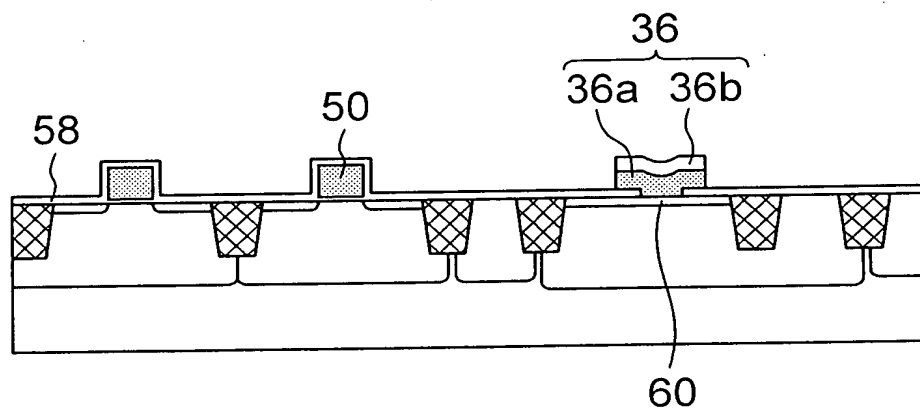


FIG. 11D

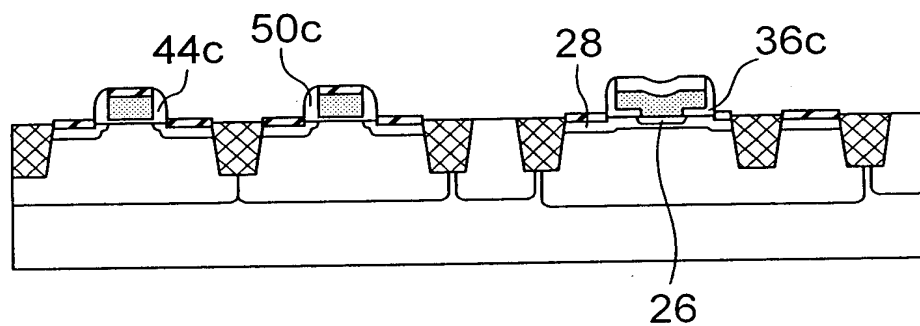


FIG. 11E

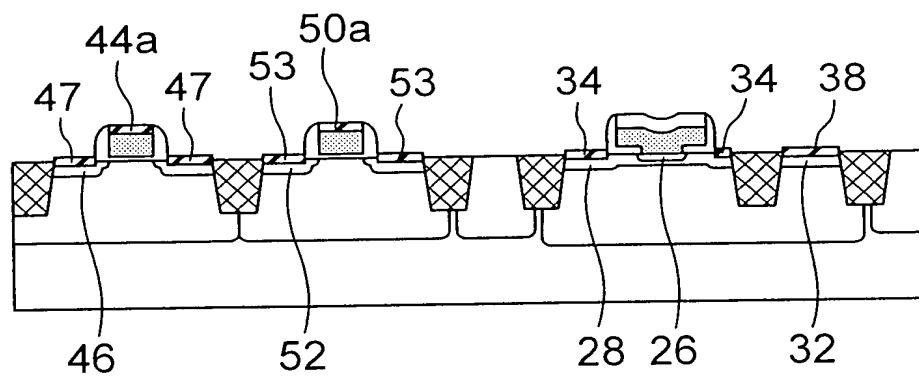


FIG. 11F

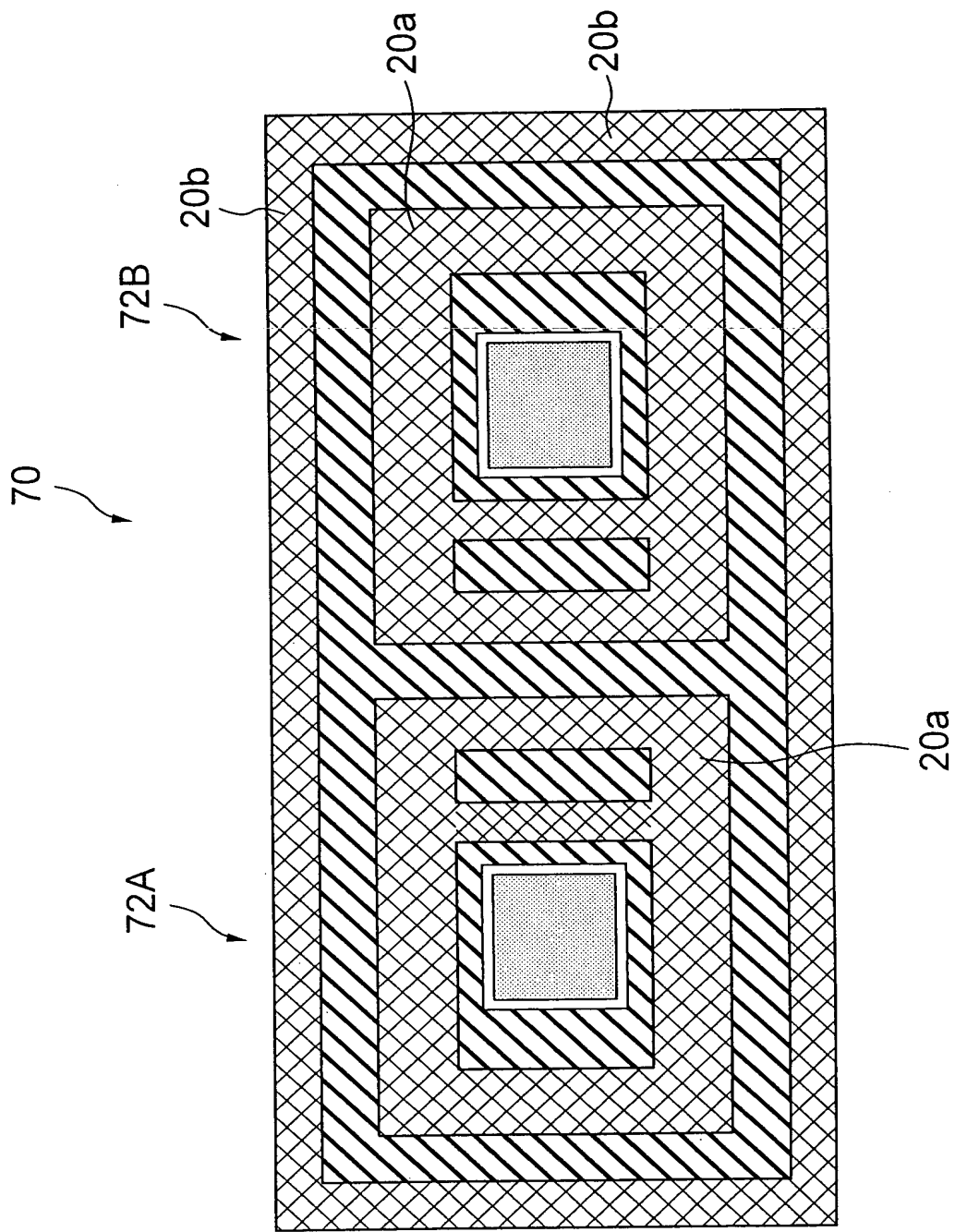


FIG. 12

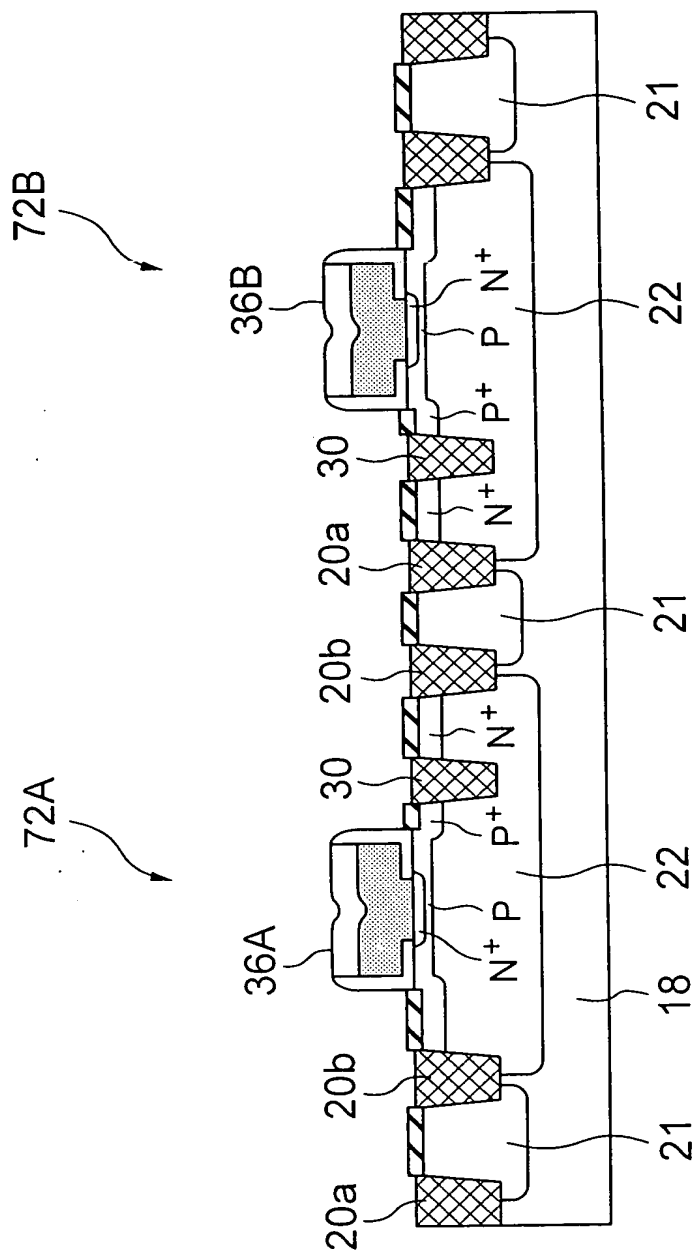


FIG. 13



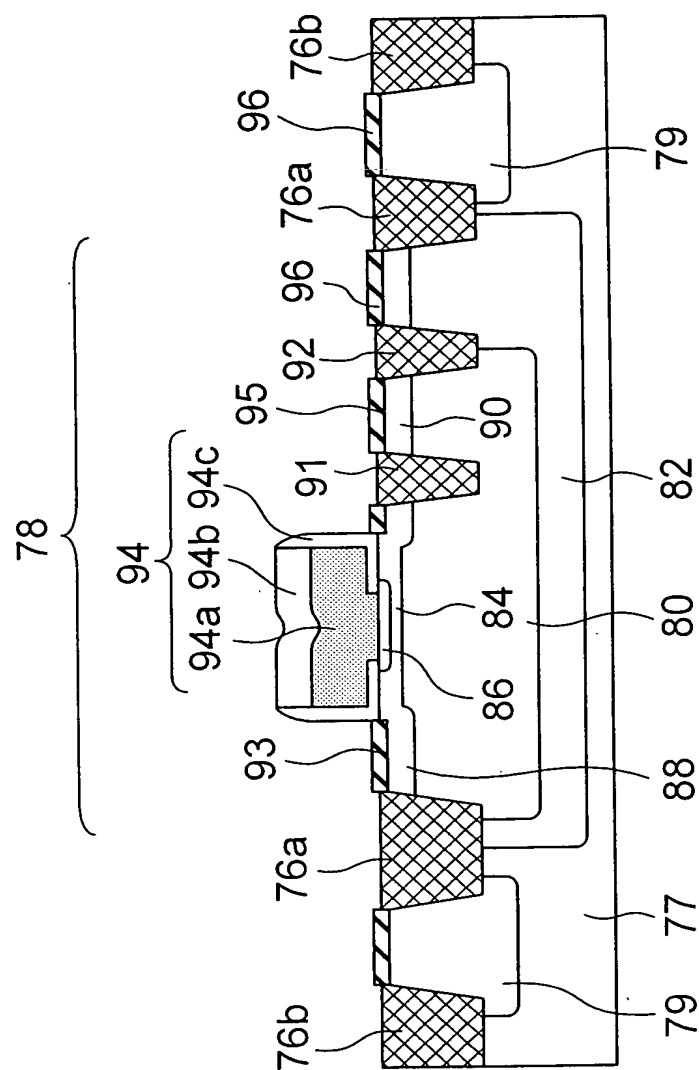


FIG. 15

A cross-sectional view of a semiconductor device 97. The device features a central core 36, which is a square region with a fine grid pattern. This core is surrounded by a first layer 98a, which is a rectangular region with a diagonal hatching pattern. The first layer 98a is further surrounded by a second layer 98b, which is a rectangular region with a diagonal hatching pattern. The second layer 98b is further surrounded by a third layer 98c, which is a rectangular region with a diagonal hatching pattern. The third layer 98c is further surrounded by a fourth layer 99a, which is a rectangular region with a diagonal hatching pattern. The fourth layer 99a is further surrounded by a fifth layer 99b, which is a rectangular region with a diagonal hatching pattern. The entire device is enclosed within a rectangular frame 97, which is a rectangular region with a diagonal hatching pattern.

FIG. 16